

# NE5550279A

R09DS0033EJ0200

Rev.2.00

Jul 04, 2012

## Silicon Power LDMOS FET

### FEATURES

- High Output Power :  $P_{out} = 33.0$  dBm TYP. ( $V_{DS} = 7.5$  V,  $I_{Dset} = 40$  mA,  $f = 460$  MHz,  $P_{in} = 15$  dBm)
- High power added efficiency :  $\eta_{add} = 68\%$  TYP. ( $V_{DS} = 7.5$  V,  $I_{Dset} = 40$  mA,  $f = 460$  MHz,  $P_{in} = 15$  dBm)
- High Linear gain :  $G_L = 22.5$  dB TYP. ( $V_{DS} = 7.5$  V,  $I_{Dset} = 40$  mA,  $f = 460$  MHz,  $P_{in} = 0$  dBm)
- High ESD tolerance
- Suitable for VHF to UHF-BAND Class-AB power amplifier.

### APPLICATIONS

- 150 MHz Band Radio System
- 460 MHz Band Radio System
- 900 MHz Band Radio System

### ORDERING INFORMATION

Part Number	Order Number	Package	Marking	Supplying Form
NE5550279A	NE5550279A-A	79A (Pb Free)	W7	<ul style="list-style-type: none"> <li>• 12 mm wide embossed taping</li> <li>• Gate pin faces the perforation side of the tape</li> </ul>
NE5550279A-T1	NE5550279A-T1-A			<ul style="list-style-type: none"> <li>• 12 mm wide embossed taping</li> <li>• Gate pin faces the perforation side of the tape</li> <li>• Qty 1 kpcs/reel</li> </ul>
NE5550279A-T1A	NE5550279A-T1A-A			<ul style="list-style-type: none"> <li>• 12 mm wide embossed taping</li> <li>• Gate pin faces the perforation side of the tape</li> <li>• Qty 5 kpcs/reel</li> </ul>

**Remark** To order evaluation samples, please contact your nearby sales office.

Part number for sample order: NE5550279A

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ , unless otherwise specified)

Operation in excess of any one of these parameters may result in permanent damage.

Parameter	Symbol	Ratings	Unit
Drain to Source Voltage	$V_{DS}$	30	V
Gate to Source Voltage	$V_{GS}$	6.0	V
Drain Current	$I_{DS}$	0.6	A
Drain Current (50% Duty Pulsed)	$I_{DS-pulse}$	1.2	A
Total Power Dissipation <sup>Note</sup>	$P_{tot}$	6.25	W
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Note: Value at  $T_C = 25^\circ\text{C}$

### CAUTION

Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The mark <R> shows major revised points.

The revised points can be easily searched by copying an "<R>" in the PDF file and specifying it in the "Find what:" field.

**RECOMMENDED OPERATING RANGE (T<sub>A</sub> = 25°C)**

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	V <sub>DS</sub>		–	7.5	9.0	V
Gate to Source Voltage	V <sub>GS</sub>		1.65	2.20	2.85	V
Drain Current	I <sub>DS</sub>		–	0.4	–	A
Input Power	P <sub>in</sub>	f = 460 MHz, V <sub>DS</sub> = 7.5 V	–	15	20	dBm

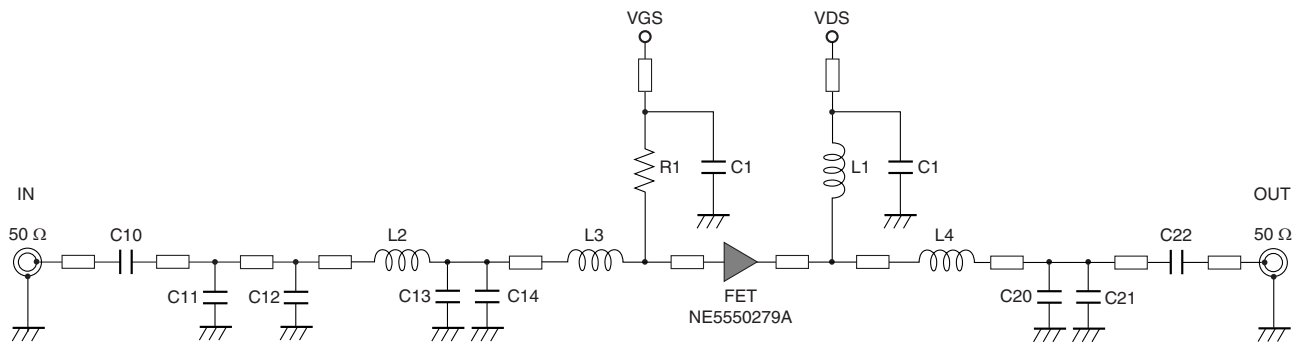
**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C, unless otherwise specified)**

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Gate to Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = 6.0 V	–	–	100	nA
Drain to Source Leakage Current (Zero Gate Voltage Drain Current)	I <sub>DSS</sub>	V <sub>DS</sub> = 25 V	–	–	10	μA
Gate Threshold Voltage	V <sub>th</sub>	V <sub>DS</sub> = 7.5 V, I <sub>DS</sub> = 1.0 mA	1.15	1.65	2.25	V
Drain to Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>DS</sub> = 10 μA	25	38	–	V
Transconductance	G <sub>m</sub>	V <sub>DS</sub> = 7.5 V, I <sub>DS</sub> = 140±20 mA	0.36	0.44	0.58	S
Thermal Resistance	R <sub>th</sub>	Channel to Case	–	20.0	–	°C/W
RF Characteristics						
Output Power	P <sub>out</sub>	f = 460 MHz, V <sub>DS</sub> = 7.5 V,	31.5	33.0	–	dBm
Drain Current	I <sub>DS</sub>	P <sub>in</sub> = 15 dBm,	–	0.38	–	A
Power Drain Efficiency	η <sub>d</sub>	I <sub>Dset</sub> = 40 mA (RF OFF)	–	70	–	%
Power Added Efficiency	η <sub>add</sub>		–	68	–	%
Linear Gain	G <sub>L</sub> <sup>Note</sup>		–	22.5	–	dB

Note: P<sub>in</sub> = 0 dBm

**Remark** DC performance is 100% testing. RF performance is testing several samples per wafer.  
Wafer rejection criteria for standard devices is 1 reject for several samples.

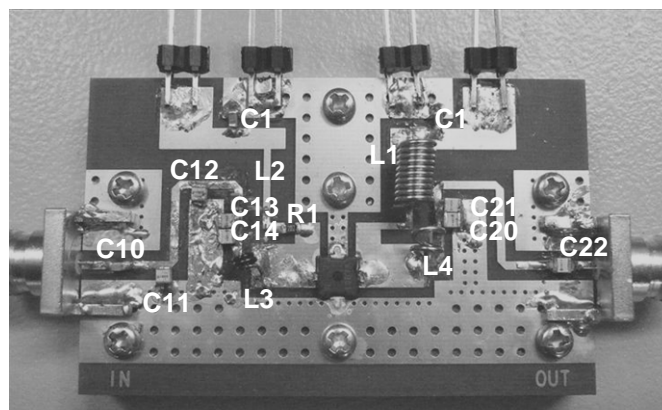
## TEST CIRCUIT SCHEMATIC FOR 460 MHz



## COMPONENTS OF TEST CIRCUIT FOR MEASURING ELECTRICAL CHARACTERISTICS

Symbol	Value	Type	Maker
C1	1 $\mu$ F	GRM188B31C105KA92	Murata
C10	22 pF	GRM1882C1H220JA01	Murata
C11	1.2 pF	ATC100A1R2JW	American Technical Ceramics
C12	4.7 pF	ATC100A4R7BW	American Technical Ceramics
C13	15 pF	ATC100A150BW	American Technical Ceramics
C14	12 pF	ATC100A120BW	American Technical Ceramics
C20	10 pF	ATC100A100JW	American Technical Ceramics
C21	3.9 pF	ATC100A3R9BW	American Technical Ceramics
C22	100 pF	ATC100A101JW	American Technical Ceramics
R1	2 k $\Omega$	1/10 W Chip Resistor RK73B1JTTD202J	KOA
L1	123 nH	$\phi$ 0.5 mm, $\phi$ D = 3 mm, 10 Turns	Ohesangyou
L2	10 nH	LQW18AN10NG00	Murata
L3	9.8 nH	$\phi$ 0.4 mm, $\phi$ D = 1.6 mm, 3 Turns	Ohesangyou
L4	20 nH	$\phi$ 0.5 mm, $\phi$ D = 3 mm, 2 Turns	Ohesangyou
PCB	-	R4775, t = 0.4 mm, $\epsilon$ r = 4.5, size = 30 $\times$ 48 mm	Panasonic
SMA Connector	-	WAKA 01K0790-20	WAKA

## COMPONENT LAYOUT OF TEST CIRCUIT FOR 460 MHz

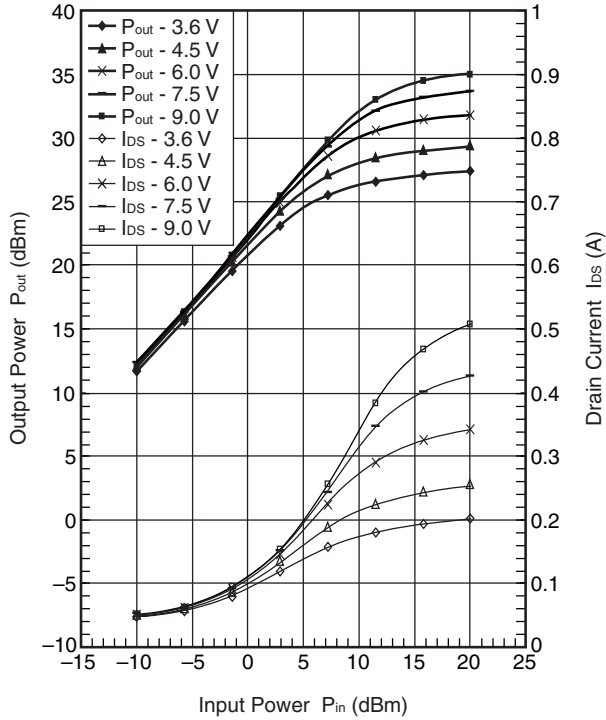


TYPICAL CHARACTERISTICS 1 (T<sub>A</sub> = 25°C)

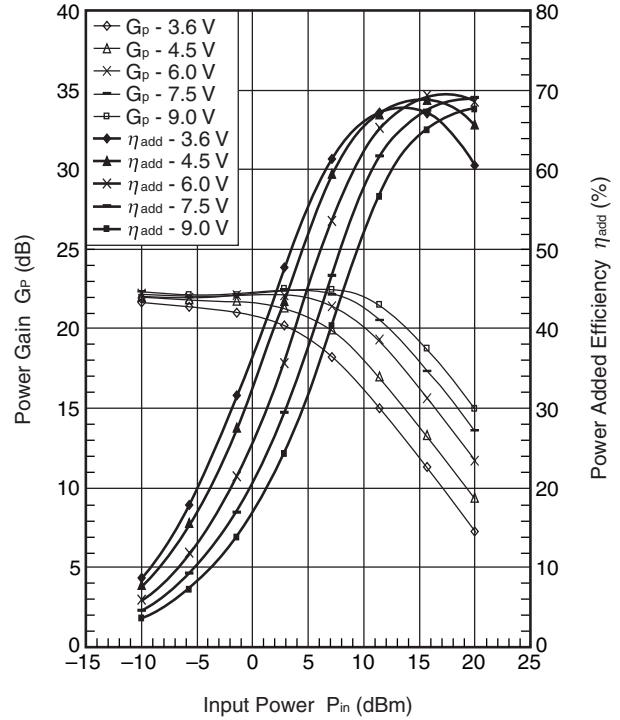
R: f = 460 MHz, V<sub>DS</sub> = 3.6/4.5/6/7.5/9 V, I<sub>Dset</sub> = 40 mA, P<sub>in</sub> = -10 to 20 dBm

IM: f1 = 460 MHz, f2 = 461 MHz, V<sub>DS</sub> = 3.6/4.5/6/7.5/9 V, I<sub>Dset</sub> = 40 mA, P<sub>out</sub> (2 tone) = 8 to 32 dBm

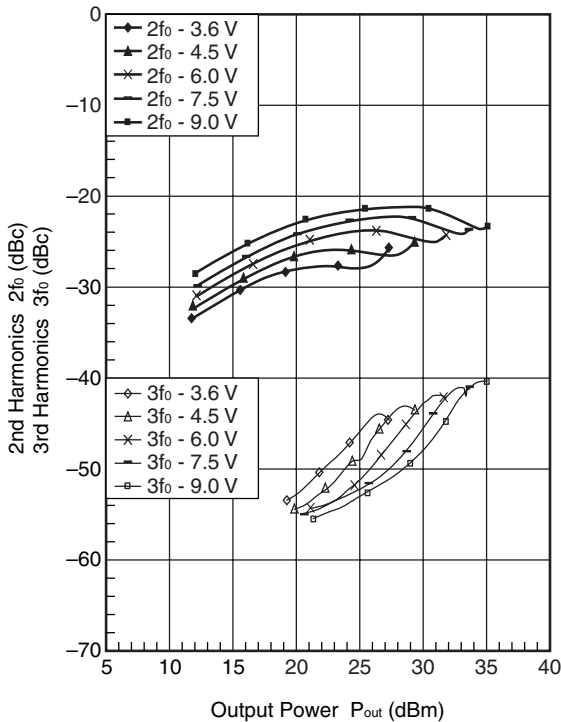
OUTPUT POWER, DRAIN CURRENT vs. INPUT POWER



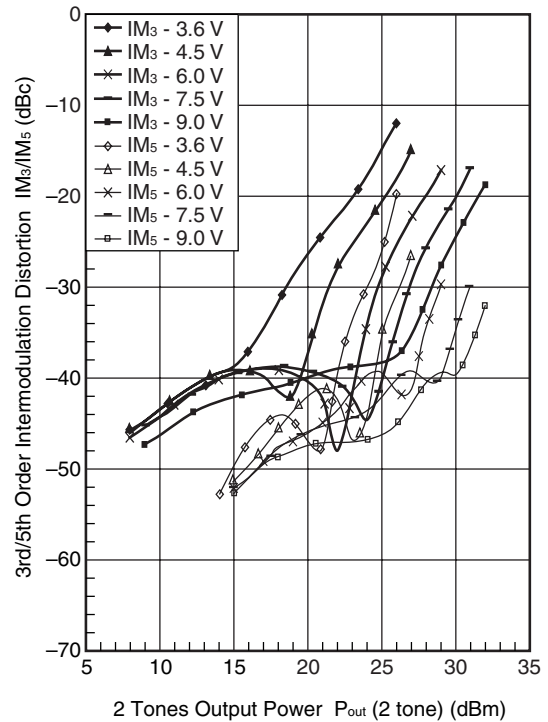
POWER GAIN, POWER ADDED EFFICIENCY vs. INPUT POWER



2f<sub>0</sub>, 3f<sub>0</sub> vs. OUTPUT POWER



IM<sub>3</sub>/IM<sub>5</sub> vs. 2 TONES OUTPUT POWER



**Remark** The graphs indicate nominal characteristics.

## S-PARAMETERS

S-parameters and noise parameters are provided on our web site in a form (S2P) that enables direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.

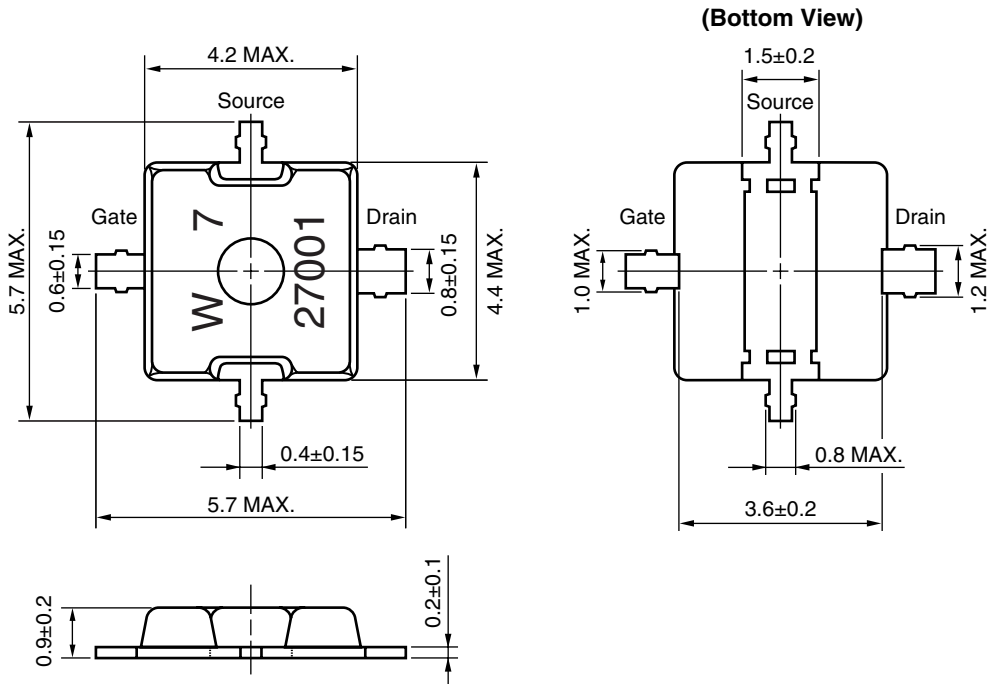
Click here to download S-parameters.

[Products] → [RF Devices] → [Device Parameters]

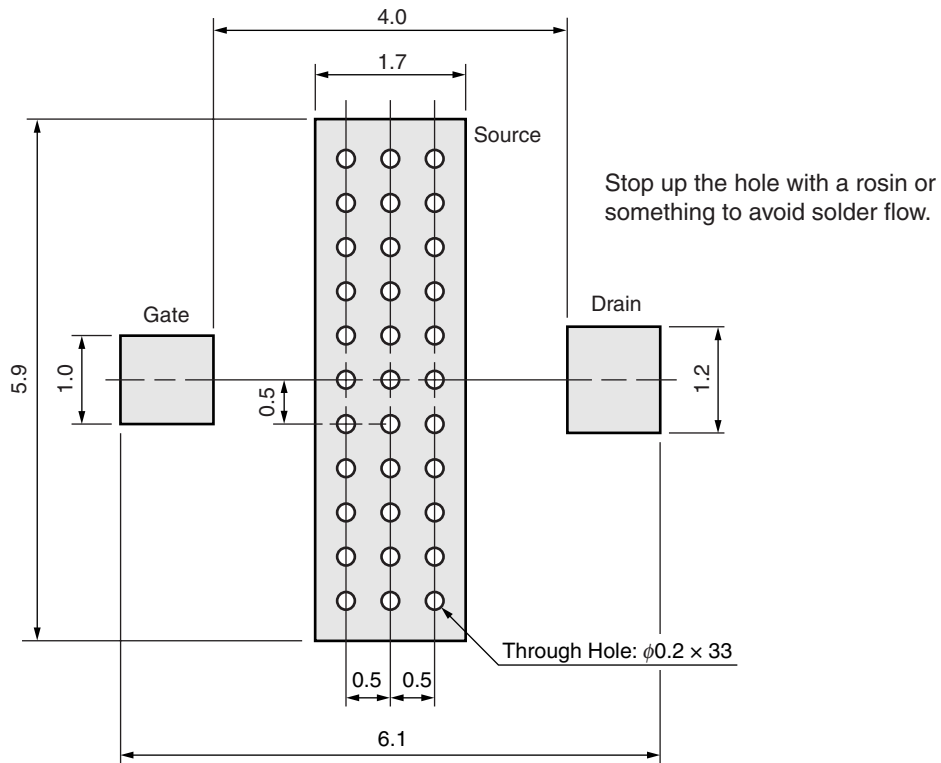
URL <http://www.renesas.com/products/microwave/>

**PACKAGE DIMENSIONS**

79A (UNIT: mm)



**79A PACKAGE RECOMMENDED P.C.B. LAYOUT (UNIT: mm)**





<b>Revision History</b>	<b>NE5550279A Data Sheet</b>
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Rev.	Date	Description	
		Page	Summary
1.00	Mar 28, 2012	-	First edition issued
2.00	Jul 04, 2012	p.2	Modification of ELECTRICAL CHARACTERISTICS

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**Renesas Electronics America Inc.**  
2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A.  
Tel: +1-408-588-6000, Fax: +1-408-588-6130

**Renesas Electronics Canada Limited**  
1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada  
Tel: +1-905-898-5441, Fax: +1-905-898-3220

**Renesas Electronics Europe Limited**  
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.  
Tel: +44-1628-585-100, Fax: +44-1628-585-900

**Renesas Electronics Europe GmbH**  
Arcadiastrasse 10, 40472 Düsseldorf, Germany  
Tel: +49-211-65030, Fax: +49-211-6503-1327

**Renesas Electronics (China) Co., Ltd.**  
7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China  
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

**Renesas Electronics (Shanghai) Co., Ltd.**  
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China  
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

**Renesas Electronics Hong Kong Limited**  
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong  
Tel: +852-2886-9318, Fax: +852 2886-9022/9044

**Renesas Electronics Taiwan Co., Ltd.**  
13F, No. 363, Fu Shing North Road, Taipei, Taiwan  
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

**Renesas Electronics Singapore Pte. Ltd.**  
1 HarbourFront Avenue, #06-10, Keppel Bay Tower, Singapore 098632  
Tel: +65-6213-0200, Fax: +65-6278-8001

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Tel: +60-3-7955-3390, Fax: +60-3-7955-9510

**Renesas Electronics Korea Co., Ltd.**  
11F., Samik Laved or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea  
Tel: +82-2-558-3737, Fax: +82-2-558-5141